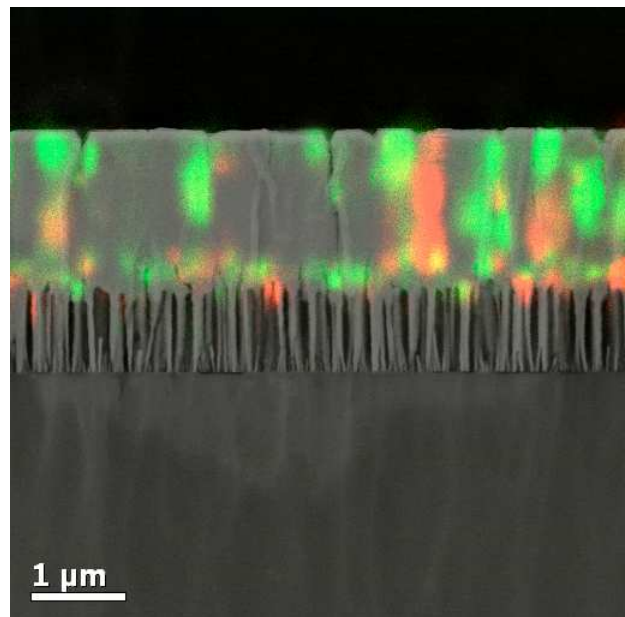


## Anna Reszka @ Paul-Drude-Institut für Festkörperelektronik, Berlin

From 5.06.2016 till 11.06.2016 I was visiting Paul-Drude-Institut für Festkörperelektronik in Berlin. Under supervision of Dr. Uwe Jahn, I participated in scanning electron microscopy and cathodoluminescence measurements at room and liquid helium temperature of III-V nanowires grown by molecular beam epitaxy technique in the Institute of Physics PAS (IP PAS) as well as in PDI. Jointly with German scientists we analysed and interpreted results. We were also discussing and comparing the results obtained earlier in our laboratories on GaN/AlGaN nanowires in order to deepen the data interpretation.

One of core-research areas of Semiconductor Spectroscopy group at PDI is the physics of III-V Nanowires and heterostructures for optoelectronic applications. Due to similar research profiles of our groups, I had an opportunity to deepen my knowledge about nitride nanowires luminescent properties and develop my skills in cathodoluminescence. The acquired skills will help me to improve my everyday research work, carried out in the Group of Electron Microscopy and Electron Spectroscopy at IP PAS. Discussions and data exchange with experts in topic of nanowire luminescence will lead to wider understanding of processes taking place in them and help in the interpretation of the results of our research in IP PAS.



Moreover, I hope that my visit in PDI laboratories and discussions with German experts will help to explain some experimental observations we made recently, in particular on luminescent properties of strained GaN/AlGaN NW structures. In addition, my visit was the continuation of research contacts between IP PAS and PDI, which have been established owing to ERASMUS Programme.